PACE 6/19 * RCVD AT 3/3/2004 3:44:09 PM [Eastern Standard Time] * SVR:USPTO EFXRF-1/1 * DNIS:8729319 * CSID:908 5/8 7795 * DURATION (mm-ss):09-16 ATTY DOCKET NO. 10/039,284 sessionental.... INFORMATION DISCLOSURE CITATION Richard A. Blanchard et al. (Use several sheets if necessary) GROUP FILING 2811 12/31/01 U.S. PATENT DOCUMENTS FILING DATE SUBCLASS CLASS NAME EXAMINER DOCUMENT NUMBER DATE IF APPROPRIATE INITIAL 12/31/2001 Blanchard 10/039,241 12/31/2001 Blanchard 10/038,845 10/4/2001 Blanchard et al. 09/970.758 DU 138 438 12/20/2001 Deboy et al. 2001/0053568A1 DV 270 438 2001/0036704A1 11/1/2001 Hucting et al DC 438 268 Hattori et al. 16/4/2001 2001/0026977A1 257 493 6/1/93 Cheo 5.216.275 63 437 Tanigawa et al. 4/28/92 5,108,783 357 23.4 1/9/90 Blanchard 4,893,160 20 437 12/8/87 Lammert 4,711,017 FOREIGN PATENT DOCUMENTS TRANSLATION SUBCLASS CLAS8 DATE COUNTRY DOCUMENT NUMBER YES NΩ OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Xing Bi Chen et al., "A Novel High-Voltage Sustaining Structure with Buried Oppositely Doped Regions," IEEE Transactions on Electron Devices, Vol. 47, No. 6, June 2000, pp. 1280-1285. R N. Cezac et al.. "A New Generation of Power Unipolar Devices: the Concept of the FLoating Islands MOS Transistor (FLIMOST)," Proceedings of the 12th International Symposium on Power Semiconductor Devices & ICs, Toulouse, France, May 22-25, 2000, pp. 69-72. P^{C} DATE CONSIDERED 3/11/04 **EXAMINER** PHAT X, CAO "EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10/039,284
				Filing Date	12/31/01
				First Named Inventor	Richard A. Blonchard et al.
				Group Art Unit	2814
				Examiner Name	Phat X. Cao
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Examiner Cite Initials* No.		U.S. Pate	ent Document	Name of Patentee or Applicant	Date of Publication of Cited Document MM- DD-YYYY	
	No.	Number	Class/Subclass	of Cited Document		
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